TL081, TL081A, TL081B, TL082, TL082A, TL082B TL082Y, TL084, TL084A, TL084B, TL084Y JFET-INPUT OPERATIONAL AMPLIFIERS

SLOS081E - FEBRUARY 1977 - REVISED FEBRUARY 1999

- Low Power Consumption
- Wide Common-Mode and Differential Voltage Ranges
- Low Input Bias and Offset Currents
- Output Short-Circuit Protection
- Low Total Harmonic Distortion . . . 0.003% Typ

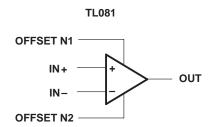
- High Input Impedance . . . JFET-Input Stage
- Latch-Up-Free Operation
- High Slew Rate . . . 13 V/μs Typ
- Common-Mode Input Voltage Range Includes V_{CC+}

description

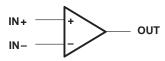
The TL08x JFET-input operational amplifier family is designed to offer a wider selection than any previously developed operational amplifier family. Each of these JFET-input operational amplifiers incorporates well-matched, high-voltage JFET and bipolar transistors in a monolithic integrated circuit. The devices feature high slew rates, low input bias and offset currents, and low offset voltage temperature coefficient. Offset adjustment and external compensation options are available within the TL08x family.

The C-suffix devices are characterized for operation from 0° C to 70° C. The I-suffix devices are characterized for operation from -40° C to 85° C. The Q-suffix devices are characterized for operation from -40° C to 125° C. The M-suffix devices are characterized for operation over the full military temperature range of -55° C to 125° C.

symbols



TL082 (EACH AMPLIFIER) TL084 (EACH AMPLIFIER)



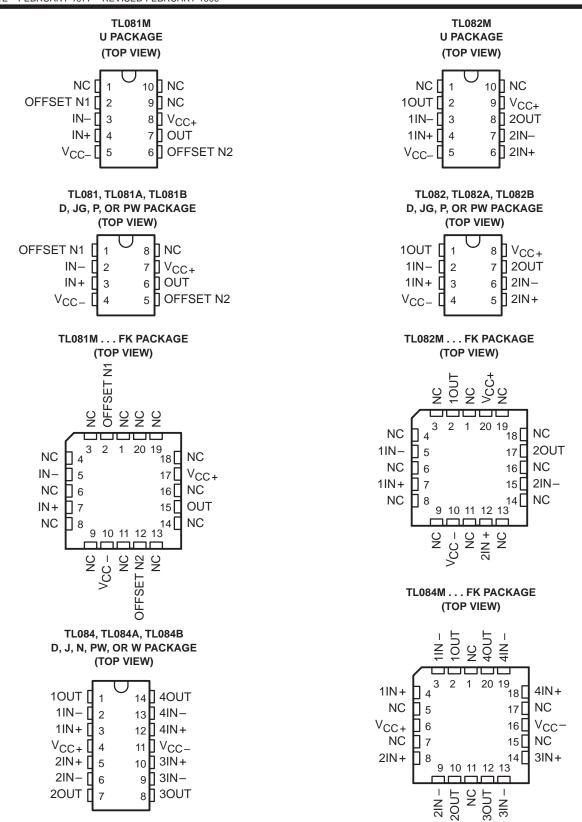


Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



TL081, TL081A, TL081B, TL082, TL082A, TL082B TL082Y, TL084, TL084A, TL084B, TL084Y JFET-INPUT OPERATIONAL AMPLIFIERS

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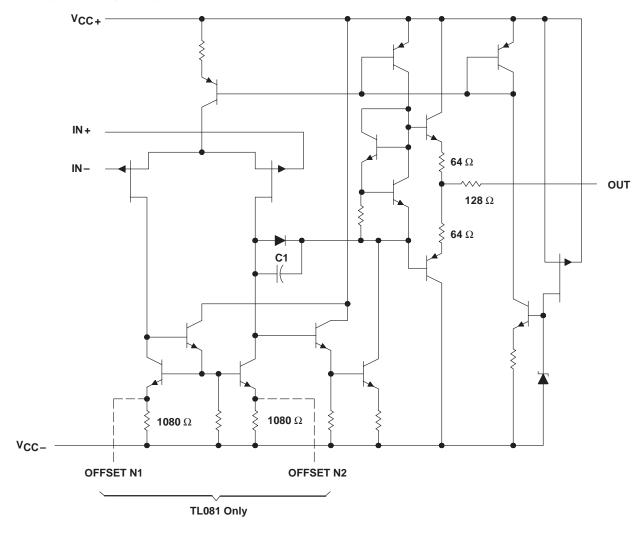
NC - No internal connection

AVAILABLE OPTIONS

						PACKAGED	DEVICES					CHIP
TA	V _{IO} max AT 25°C	SMALL OUTLINE (D008)	SMALL OUTLINE (D014)	CHIP CARRIER (FK)	CERAMIC DIP (J)	CERAMIC DIP (JG)	PLASTIC DIP (N)	PLASTIC DIP (P)	TSSOP (PW)	FLAT PACK (U)	FLAT PACK (W)	FORM (Y)
	15 mV 6 mV 3 mV	TL081CD TL081ACD TL081BCD	_	_	_	_	_	TL081CP TL081ACP TL081BCP	TL081CPW	_		_
0°C to 70°C	15 mV 6 mV 3 mV	TL082CD TL082ACD TL082BCD	_	_	_	_	_	TL082CP TL082ACP TL082BCP	TL082CPW	_		TL082Y
	15 mV 6 mV 3 mV	_	TL084CD TL084ACD TL084BCD	_	_	_	TL084CN TL084ACN TL084BCN	_	TL084CPW	_	_	TL084Y
-40°C to 85°C	6 mV 6 mV 6 mV	TL081ID TL082ID TL084ID	TL084ID	_	_	_	TL084IN	TL081IP TL082IP	_	_	_	_
-40°C to 125°C	9 mV	_	TL084QD	_	_	_	-	_	_	ı	-	-
-55°C to 125°C	6 mV 6 mV 9 mV	_	_	TL081MFK TL082MFK TL084MFK	TL084MJ	TL081MJG TL082MJG	_	_	_	TL081MU TL082MU	TL084MW	_

The D package is available taped and reeled. Add R suffix to the device type (e.g., TL081CDR).

schematic (each amplifier)

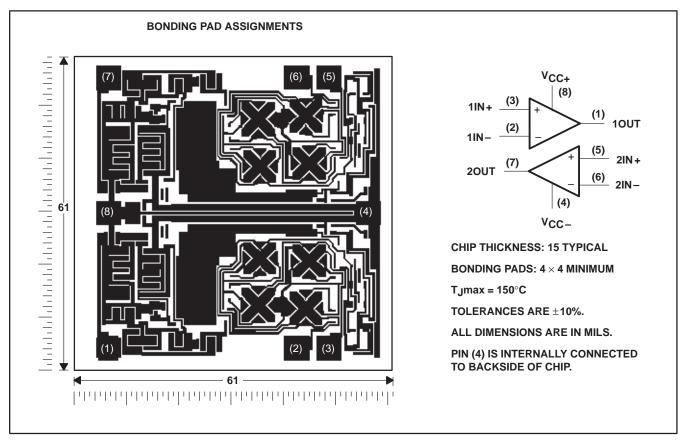


Component values shown are nominal.



TL082Y chip information

These chips, when properly assembled, display characteristics similar to the TL082. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. Chips may be mounted with conductive epoxy or a gold-silicon preform.

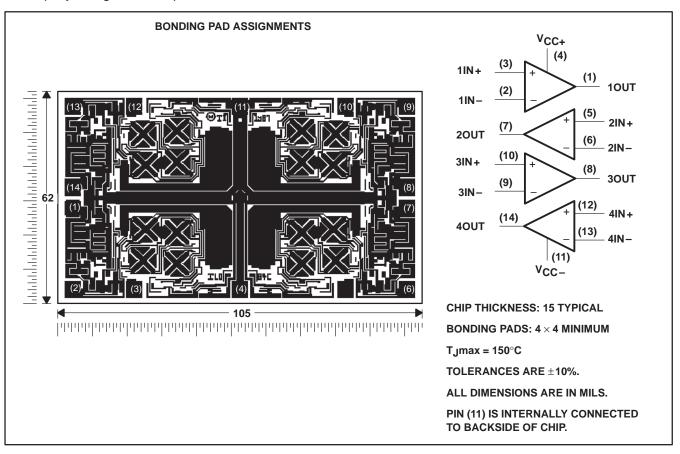


TL081, TL081A, TL081B, TL082, TL082A, TL082B TL082Y, TL084, TL084A, TL084B, TL084Y JFET-INPUT OPERATIONAL AMPLIFIERS

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TL084Y chip information

These chips, when properly assembled, display characteristics similar to the TL084. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. Chips may be mounted with conductive epoxy or a gold-silicon preform.



TL081, TL081A, TL081B, TL082, TL082A, TL082B TL082Y, TL084, TL084A, TL084B, TL084Y JFET-INPUT OPERATIONAL AMPLIFIERS

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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

		TL08_C TL08_AC TL08_BC	TL08_I	TL084Q	TL08_M	UNIT					
Supply voltage, V _{CC+} (see Note 1)		18	18	18	18	V					
Supply voltage V _{CC} – (see Note 1)	-18	-18	-18	-18	V						
Differential input voltage, V _{ID} (see Note 2)	± 30	± 30	± 30	± 30	V						
Input voltage, V _I (see Notes 1 and 3)	±15	±15	±15	±15	V						
Duration of output short circuit (see Note 4)	unlimited	unlimited	unlimited	unlimited							
Continuous total power dissipation	Continuous total power dissipation				See Dissipation Rating Table						
Operating free-air temperature range, TA		0 to 70	- 40 to 85	- 40 to 125	- 55 to 125	°C					
Storage temperature range, T _{Stg}		- 65 to 150	- 65 to 150	- 65 to 150	- 65 to 150	°C					
Case temperature for 60 seconds, T _C	FK package				260	°C					
Lead temperature 1,6 mm (1/16 inch) from case for 60 seconds	J or JG package				300	°C					
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	D, N, P, or PW package	260	260	260		°C					

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltage values, except differential voltages, are with respect to the midpoint between VCC+ and VCC-.

- 2. Differential voltages are at IN+ with respect to IN-.
- 3. The magnitude of the input voltage must never exceed the magnitude of the supply voltage or 15 V, whichever is less.
- 4. The output may be shorted to ground or to either supply. Temperature and/or supply voltages must be limited to ensure that the dissipation rating is not exceeded.

DISSIPATION RATING TABLE

PACKAGE	T _A ≤ 25°C POWER RATING	DERATING FACTOR	DERATE ABOVE T _A	T _A = 70°C POWER RATING	T _A = 85°C POWER RATING	T _A = 125°C POWER RATING
D (8 pin)	680 mW	5.8 mW/°C	32°C	460 mW	373 mW	N/A
D (14 pin)	680 mW	7.6 mW/°C	60°C	604 mW	490 mW	186 mW
FK	680 mW	11.0 mW/°C	88°C	680 mW	680 mW	273 mW
J	680 mW	11.0 mW/° C	88°C	680 mW	680 mW	273 mW
JG	680 mW	8.4 mW/°C	69°C	672 mW	546 mW	210 mW
N	680 mW	9.2 mW/°C	76°C	680 mW	597 mW	N/A
Р	680 mW	8.0 mW/°C	65°C	640 mW	520 mW	N/A
PW (8 pin)	525 mW	4.2 mW/°C	25°C	336 mW	N/A	N/A
PW (14 pin)	700 mW	5.6 mW/°C	25°C	448 mW	N/A	N/A
U	675 mW	5.4 mW/°C	25°C	432 mW	351 mW	135 mW
W	680 mW	8.0 mW/°C	65°C	640 mW	520 mW	200 mW

electrical characteristics, $V_{CC\pm} = \pm 15 \text{ V}$ (unless otherwise noted)

ı	PARAMETER	TEST CON	IDITIONS	T _A †		TL081C TL082C TL084C		1	ΓL081ΑC ΓL082ΑC ΓL084ΑC		i	TL081B0 TL082B0 TL084B0			TL081I TL082I TL084I		UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
V	Input offset voltage	V _O = 0	R _S = 50 Ω	25°C		3	15		3	6		2	3		3	6	mV
VIO	input onset voltage	vQ = 0	NS = 30 22	Full range			20			7.5			5			9	1110
ανιο	Temperature coefficient of input offset voltage	V _O = 0	R _S = 50 Ω	Full range		18			18			18			18		μV/°C
1,0	Input offset current‡	V _O = 0		25°C		5	200		5	100		5	100		5	100	рА
IIO	Input onset current+	VO = 0		Full range			2			2			2			10	nA
IB	Input bias current‡	V _O = 0		25°C		30	400		30	200		30	200		30	200	рА
ПВ	Input bias current+	VO = 0		Full range			10			7			7			20	nA
. ,	Common-mode input		I	0500	 	-12			-12			-12			-12		1 [
VICR	voltage range		!	25°C	±11	to 15		±11	to 15		±11	to 15		±11	to 15	!	V
		$R_I = 10 \text{ k}\Omega$		25°C	±12	±13.5		±12	±13.5		±12	±13.5		±12	±13.5		
V _{OM}	Maximum peak	R _L ≥ 10 kΩ		Full seases	±12			±12			±12			±12			V
	output voltage swing	$R_L \ge 2 k\Omega$		Full range	±10	±12		±10	±12		±10	±12		±10	±12		\neg
	Large-signal	$V_0 = \pm 10 \text{ V},$	$R_L \ge 2 k\Omega$	25°C	25	200		50	200		50	200		50	200		2//2/
AVD	differential voltage amplification	$V_0 = \pm 10 \text{ V},$	$R_L \ge 2 k\Omega$	Full range	15			25			25			25			V/mV
B ₁	Unity-gain bandwidth			25°C		3			3			3			3		MHz
ri	Input resistance			25°C		1012			1012			1012			1012		Ω
CMRR	Common-mode rejection ratio	$V_{IC} = V_{ICR}m_{IC}$ $V_{O} = 0$,	nin, $R_S = 50 \Omega$	25°C	70	86		75	86		75	86		75	86		dB
ksvr	Supply voltage rejection ratio (ΔV _{CC±} /ΔV _{IO})	$V_{CC} = \pm 15 \text{ V}$ $V_{O} = 0$,	$'$ to \pm 9 V, R _S = 50 Ω	25°C	70	86		80	86		80	86		80	86		dB
lcc	Supply current (per amplifier)	V _O = 0,	No load	25°C		1.4	2.8		1.4	2.8		1.4	2.8		1.4	2.8	mA
V _{O1} /V _{O2}	Crosstalk attenuation	A _{VD} = 100		25°C		120			120			120			120		dB

[†] All characteristics are measured under open-loop conditions with zero common-mode voltage unless otherwise specified. Full range for TA is 0°C to 70°C for TL08_C, TL08_AC, TL08_BC and -40°C to 85°C for TL08_I.

[‡] Input bias currents of a FET-input operational amplifier are normal junction reverse currents, which are temperature sensitive as shown in Figure 17. Pulse techniques must be used that maintain the junction temperature as close to the ambient temperature as possible.

electrical characteristics, $V_{\mbox{CC}\,\pm}$ = ± 15 V (unless otherwise noted)

	DAD AMETED	TEOT 001	IDITIONS [†]	_	TL08	31M, TL0	82M	TL08	34Q, TL0	84M	UNIT
'	PARAMETER	TEST CON	IDITIONS	TA	MIN	TYP	MAX	MIN	TYP	MAX	UNII
\/\c	Input offset voltage	VO = 0,	$R_S = 50 \Omega$	25°C		3	6		3	9	mV
VIO	input onset voltage	VO = 0,	KS = 50 12	Full range			9			15	IIIV
αΝΙΟ	Temperature coefficient of input offset voltage	V _O = 0	R _S = 50 Ω	Full range		18			18		μV/°C
lio.	Input offset current‡	V _O = 0		25°C		5	100		5	100	pА
110	input onset current+	VO = 0		125°C			20			20	nA
IIB	Input bias current‡	VO = 0		25°C		30	200		30	200	pА
IIB	input bias current+	VO = 0		125°C			50			50	nA
VICR	Common-mode input voltage range			25°C	±11	±12 to 15		±11	± 12 to 15		٧
		$R_L = 10 \text{ k}\Omega$		25°C	±12	±13.5		±12	±13.5		
VOM	Maximum peak output voltage swing	$R_L \ge 10 \text{ k}\Omega$		Full range	±12			±12			V
		$R_L \ge 2 k\Omega$		ruii range	±10	±12		±10	±12		
AVD	Large-signal differential voltage	$V_0 = \pm 10 \text{ V},$	$R_L \ge 2 \; k\Omega$	25°C	25	200		25	200		V/mV
AVD	amplification	$V_0 = \pm 10 \text{ V},$	$R_L \ge 2 \; k\Omega$	Full range	15			15			V/IIIV
B ₁	Unity-gain bandwidth			25°C		3			3		MHz
rį	Input resistance			25°C		1012			1012		Ω
CMRR	Common-mode rejection ratio	$V_{IC} = V_{ICR}n$ $V_{O} = 0$,	nin, $R_S = 50 \Omega$	25°C	80	86		80	86		dB
kSVR	Supply voltage rejection ratio ($\Delta V_{CC\pm}/\Delta V_{IO}$)	$V_{CC} = \pm 15 \ V_{O} = 0,$	' to ±9 V, R _S = 50 Ω	25°C	80	86		80	86		dB
ICC	Supply current (per amplifier)	V _O = 0,	No load	25°C		1.4	2.8		1.4	2.8	mA
V _{O1} /V _{O2}	Crosstalk attenuation	$A_{VD} = 100$		25°C		120			120		dB

[†] All characteristics are measured under open-loop conditions with zero common-mode input voltage unless otherwise specified.

operating characteristics, $V_{CC\pm}$ = ± 15 V, T_A = 25°C (unless otherwise noted)

	PARAMETER		TEST CONDIT	TONS		MIN	TYP	MAX	UNIT
		V _I = 10 V,	$R_L = 2 k\Omega$,	$C_L = 100 pF$,	See Figure 1	8*	13		
SR	Slew rate at unity gain	$V_I = 10 \text{ V},$ $T_A = -55^{\circ}\text{C to } 125^{\circ}\text{C},$	$R_L = 2 k\Omega$, See Figure 1	C _L = 100 pF,		5*			V/µs
t _r	Rise time	V _I = 20 mV,	$R_1 = 2 k\Omega$	$C_1 = 100 pF$	See Figure 1		0.05		μs
	Overshoot factor	V = 20 IIIV,	KL = 2 K12,	CL = 100 pr,	See Figure 1		20%		
\	Equivalent input noise	Pa - 20 O	f = 1 kHz				18		nV/√ Hz
V _n	voltage	$R_S = 20 \Omega$	f = 10 Hz to 1		4		μV		
In	Equivalent input noise current	$R_S = 20 \Omega$,	f = 1 kHz				0.01		pA/√ Hz
THD	Total harmonic distortion	V _I rms = 6 V, f = 1 kHz	$A_{VD} = 1$,	$R_S \le 1 \text{ k}\Omega$,	$R_L \ge 2 k\Omega$,		0.003%		

^{*}On products compliant to MIL-PRF-38535, this parameter is not production tested.



[‡] Input bias currents of a FET-input operational amplifier are normal junction reverse currents, which are temperature sensitive as shown in Figure 17. Pulse techniques must be used that maintain the junction temperatures as close to the ambient temperature as is possible.

TL081, TL081A, TL081B, TL082, TL082A, TL082B TL082Y, TL084, TL084A, TL084B, TL084Y JFET-INPUT OPERATIONAL AMPLIFIERS

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electrical characteristics, $V_{CC\pm}$ = ± 15 V, T_A = $25^{\circ}C$ (unless otherwise noted)

	PARAMETER	TEST COND	utionet	TL0	82Y, TL0	84Y	UNIT
	PARAMETER	I IESI COND	ITIONS	MIN	TYP	MAX	UNII
V _{IO}	Input offset voltage	V _O = 0,	$R_S = 50 \Omega$		3	15	mV
ανιο	Temperature coefficient of input offset voltage	$V_{O} = 0$,	$R_S = 50 \Omega$		18		μV/°C
I _{IO}	Input offset current [‡]	$V_{O} = 0$,			5	200	pА
I _{IB}	Input bias current [‡]	$V_{O} = 0$,			30	400	рА
VICR	Common-mode input voltage range			±11	-12 to 15		V
VOM	Maximum peak output voltage swing	$R_L = 10 \text{ k}\Omega$,		±12	±13.5		V
AVD	Large-signal differential voltage amplification	$V_0 = \pm 10 \text{ V},$	$R_L \ge 2 k\Omega$	25	200		V/mV
B ₁	Unity-gain bandwidth				3		MHz
rį	Input resistance				1012		Ω
CMRR	Common-mode rejection ratio	V _{IC} = V _{ICR} min,	$V_{O} = 0,$	70	86		dB
CIVILLIA	Common-mode rejection ratio	$R_S = 50 \Omega$		70	86		ub .
kovp	Supply voltage rejection ratio (ΔV _{CC+} /ΔV _{IO})	$V_{CC} = \pm 15 \text{ V to } \pm 15 \text{ V}$	9 V,	70	86		dB
ksvr	Supply voltage rejection ratio (AvCC±7Av(O)	$V_{O} = 0,$	$R_S = 50 \Omega$	70	86		uБ
ICC	Supply current (per amplifier)	$V_{O} = 0$,	No load		1.4	2.8	mA
V _{O1} /V _{O2}	Crosstalk attenuation	A _{VD} = 100			120		dB

[†] All characteristics are measured under open-loop conditions with zero common-mode voltage unless otherwise specified.

operating characteristics, $V_{\mbox{CC}\pm}$ = ± 15 V, $T_{\mbox{A}}$ = $25^{\circ}\mbox{C}$

	PARAMETER	TEST CONDITIONS					TYP	MAX	UNIT
SR	Slew rate at unity gain	V _I = 10 V,	$R_L = 2 k\Omega$,	$C_L = 100 pF$,	See Figure 1	8	13		V/µs
t _r	Rise time	V _I = 20 mV,	Pr = 2 kO	C _L = 100 pF,	See Figure 1		0.05		μs
	Overshoot factor	V = 20 IIIV,	$K_{\perp} = 2 \text{ KS2},$				20%		
\	Equivalent input noise voltage	Po - 20 O	f = 1 kHz				18		nV/√ Hz
Vn	Equivalent input noise voitage	$R_S = 20 \Omega$	f = 10 Hz to 10 kHz				4		μV
In	Equivalent input noise current	$R_S = 20 \Omega$,	f = 1 kHz				0.01		pA/√ Hz
THD	Total harmonic distortion	V _I rms = 6 V, f = 1 kHz	A _{VD} = 1,	R _S ≤ 1 kΩ,	$R_L \ge 2 k\Omega$,		0.003%		

[‡] Input bias currents of a FET-input operational amplifier are normal junction reverse currents, which are temperature sensitive as shown in Figure 17. Pulse techniques must be used that maintain the junction temperature as close to the ambient temperature as possible.

PARAMETER MEASUREMENT INFORMATION

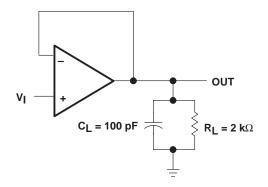


Figure 1

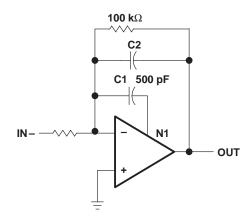


Figure 3

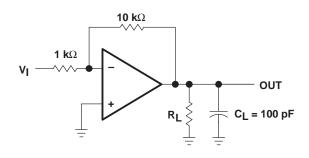


Figure 2

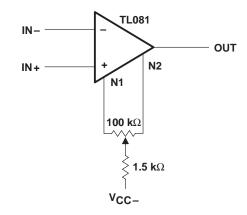


Figure 4

TYPICAL CHARACTERISTICS

Table of Graphs

			FIGURE
Vом	Maximum peak output voltage	vs Frequency vs Free-air temperature vs Load resistance vs Supply voltage	5, 6, 7 8 9 10
A _{VD}	Large-signal differential voltage amplification	vs Free-air temperature vs Frequency	11 12
	Differential voltage amplification	vs Frequency with feed-forward compensation	13
PD	Total power dissipation	vs Free-air temperature	14
Icc	Supply current	vs Free-air temperature vs Supply voltage	15 16
I _{IB}	Input bias current	vs Free-air temperature	17
	Large-signal pulse response	vs Time	18
٧o	Output voltage	vs Elapsed time	19
CMRR	Common-mode rejection ratio	vs Free-air temperature	20
Vn	Equivalent input noise voltage	vs Frequency	21
THD	Total harmonic distortion	vs Frequency	22

MAXIMUM PEAK OUTPUT VOLTAGE

FREQUENCY

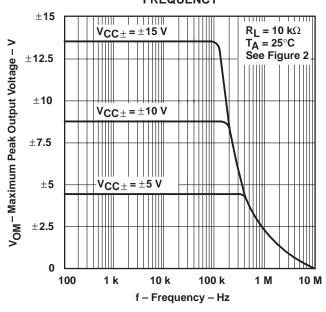


Figure 5

MAXIMUM PEAK OUTPUT VOLTAGE vs

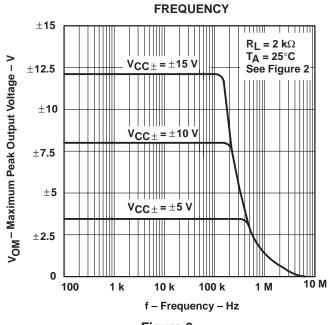


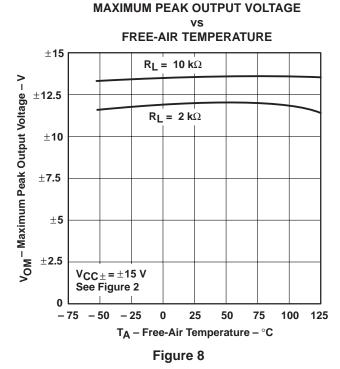
Figure 6

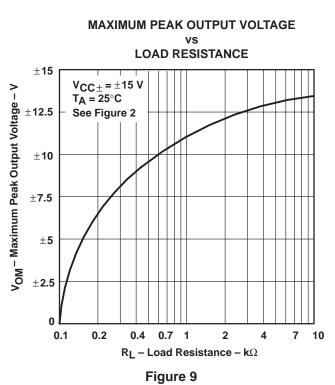


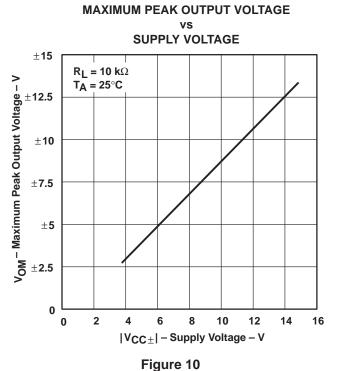
TYPICAL CHARACTERISTICS†

MAXIMUM PEAK OUTPUT VOLTAGE FREQUENCY ± 15 $V_{CC\pm} = \pm 15 \text{ V}$ V_{OM} - Maximum Peak Output Voltage - V $R_L = 2 k\Omega$ $T_A = 25^{\circ}C$ ±12.5 See Figure 2 ± 10 $T_A = -55^{\circ}C$ ± 7.5 T_A = 125°C ± 5 ±2.5 10 k 40 k 100 k 400 k 1 M 4 M 10 M f - Frequency - Hz

Figure 7







[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION

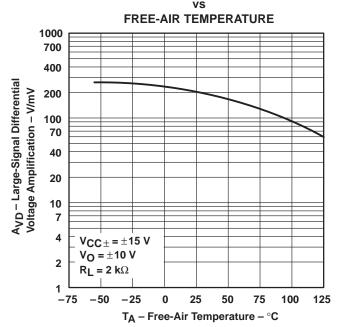


Figure 11

LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION

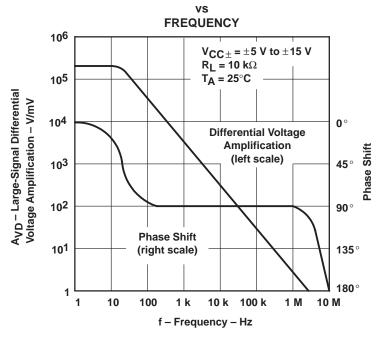


Figure 12

[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



DIFFERENTIAL VOLTAGE AMPLIFICATION FREQUENCY WITH FEED-FORWARD COMPENSATION 106 A_{VD} - Differential Voltage Amplification - V/mV $V_{CC\pm} = \pm 15 \text{ V}$ C2 = 3 pF105 $T_A = 25^{\circ}C$ See Figure 3 104 103 102 10 100 1 k 10 k 100 k 1 M 10 M

Figure 13

f - Frequency With Feed-Forward Compensation - Hz

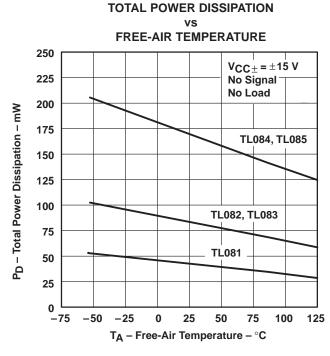
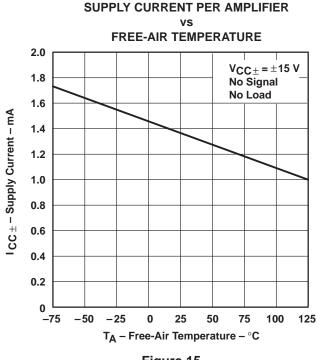
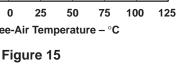
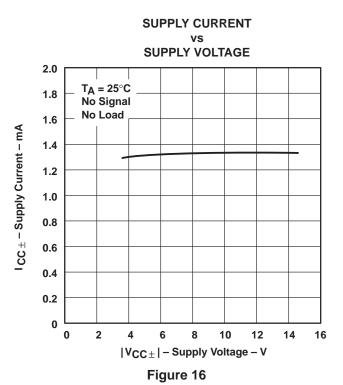


Figure 14

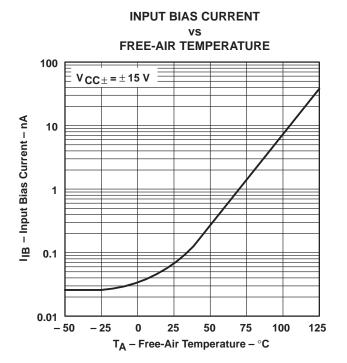






† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.





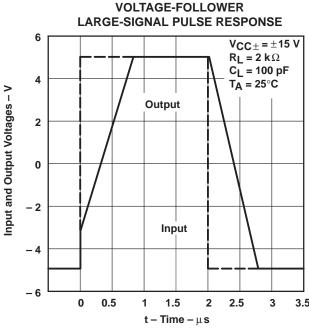
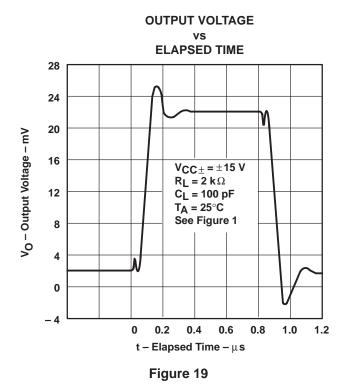


Figure 17





COMMON-MODE REJECTION RATIO FREE-AIR TEMPERATURE 89

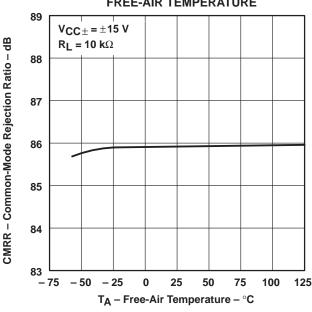
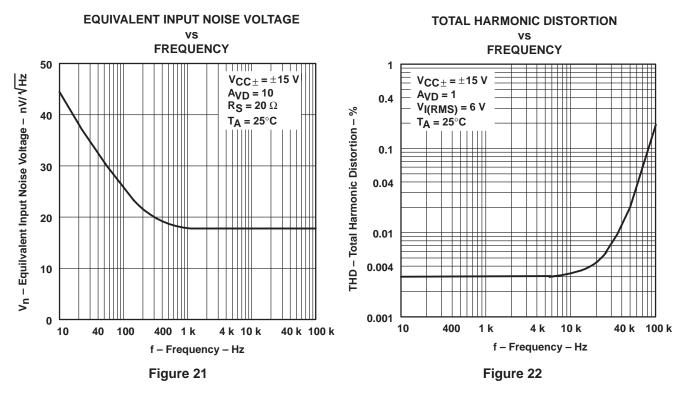


Figure 20

[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.





† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

APPLICATION INFORMATION

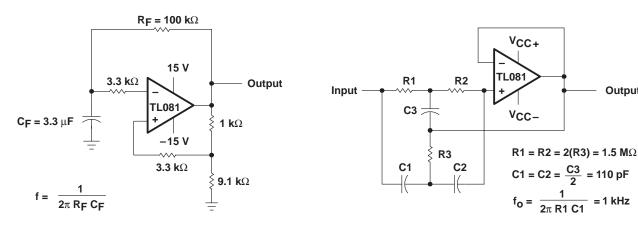


Figure 23 Figure 24

Output

APPLICATION INFORMATION

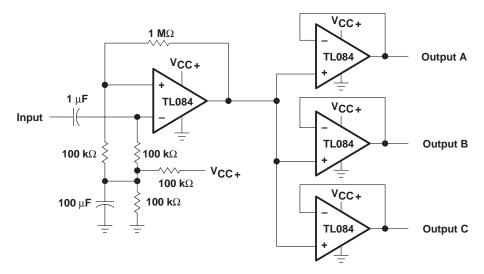
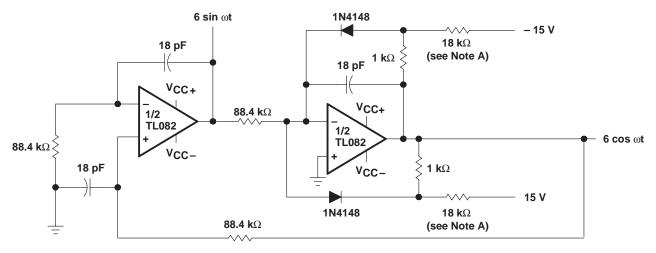


Figure 25. Audio-Distribution Amplifier



NOTE A: These resistor values may be adjusted for a symmetrical output.

Figure 26. 100-KHz Quadrature Oscillator



APPLICATION INFORMATION

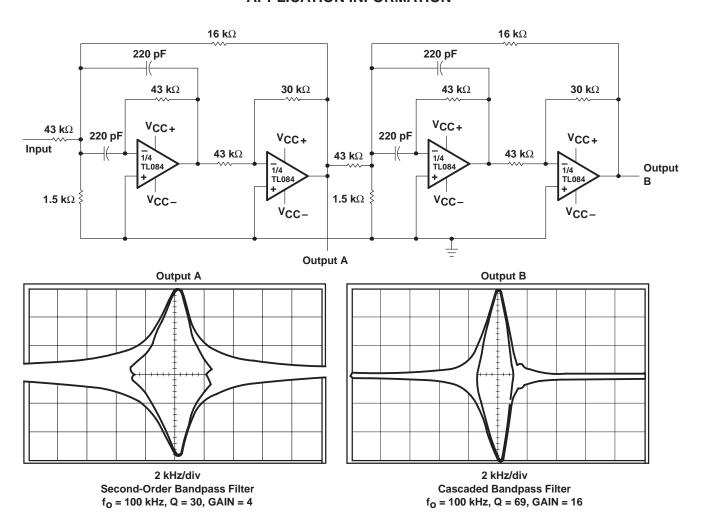


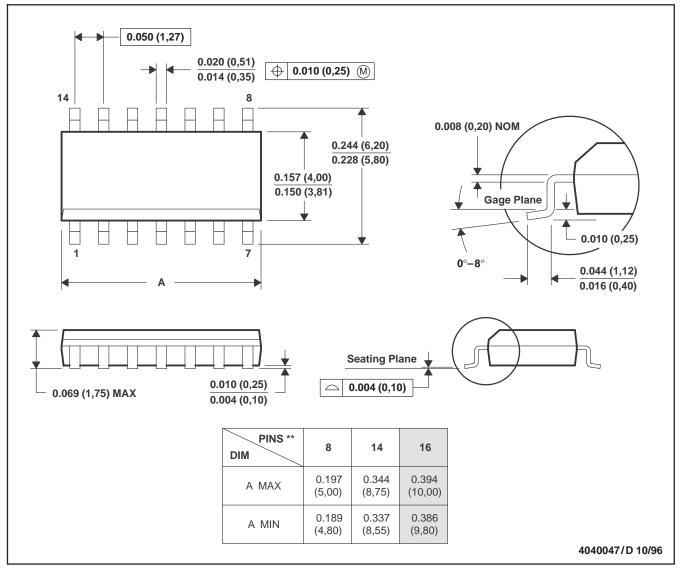
Figure 27. Positive-Feedback Bandpass Filter

MECHANICAL DATA

D (R-PDSO-G**)

14 PIN SHOWN

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion, not to exceed 0.006 (0,15).

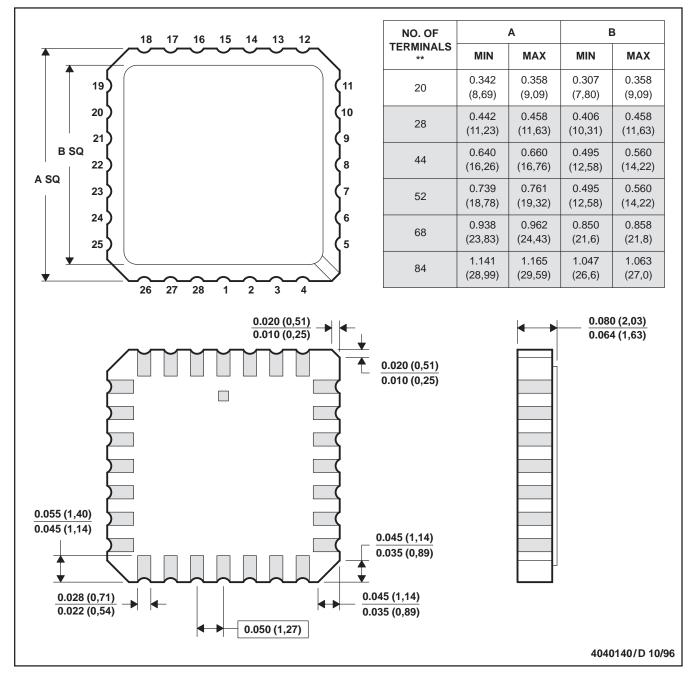
D. Falls within JEDEC MS-012

MECHANICAL DATA

FK (S-CQCC-N**)

28 TERMINAL SHOWN

LEADLESS CERAMIC CHIP CARRIER



- NOTES: A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - C. This package can be hermetically sealed with a metal lid.
 - D. The terminals are gold plated.
 - E. Falls within JEDEC MS-004

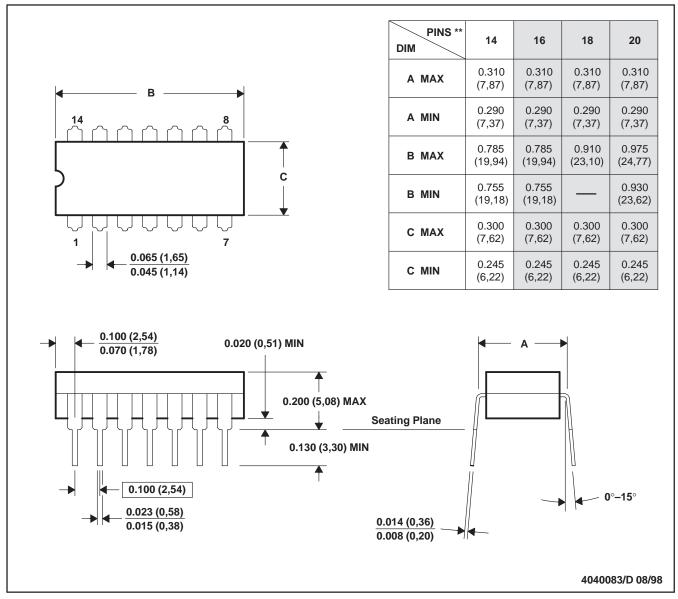


MECHANICAL DATA

J (R-GDIP-T**)

14 PIN SHOWN

CERAMIC DUAL-IN-LINE PACKAGE



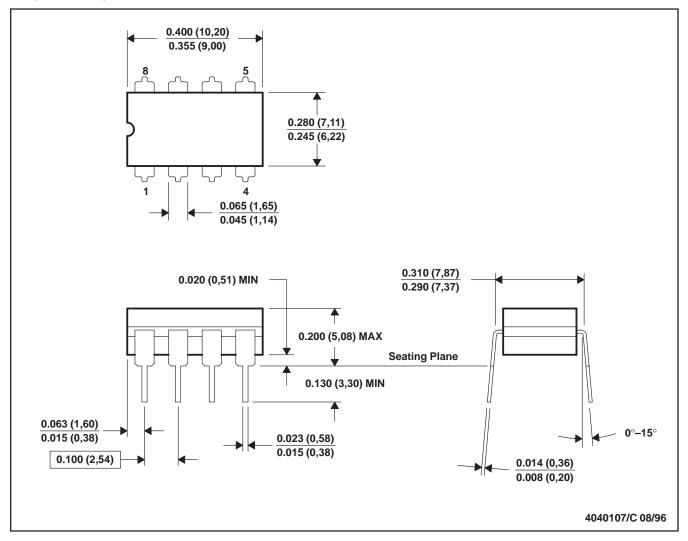
- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
- E. Falls within MIL STD 1835 GDIP1-T14, GDIP1-T16, GDIP1-T18, GDIP1-T20, and GDIP1-T22.



MECHANICAL DATA

JG (R-GDIP-T8)

CERAMIC DUAL-IN-LINE PACKAGE



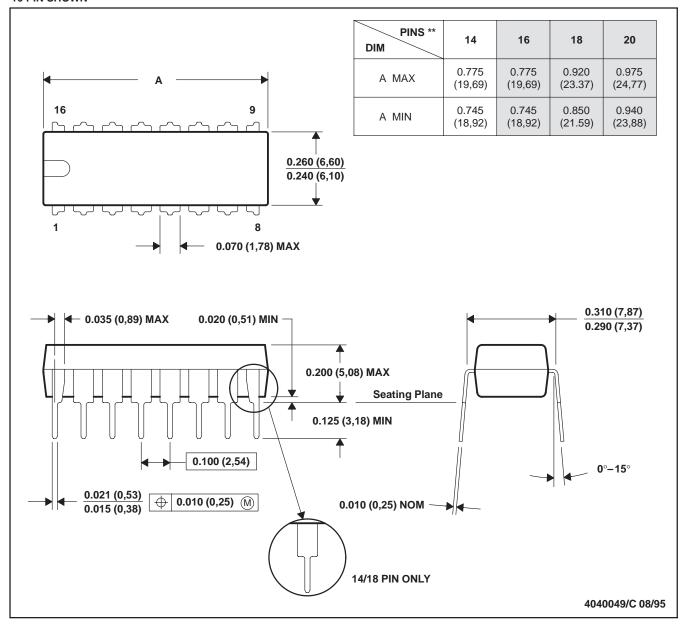
- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
- E. Falls within MIL-STD-1835 GDIP1-T8

MECHANICAL DATA

N (R-PDIP-T**)

16 PIN SHOWN

PLASTIC DUAL-IN-LINE PACKAGE



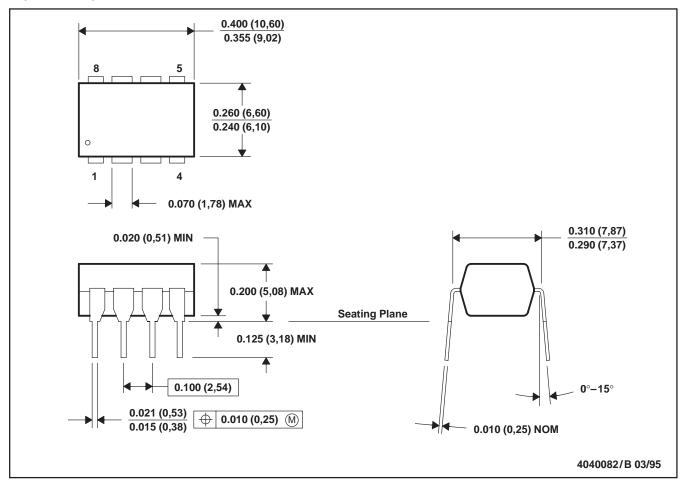
- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001 (20 pin package is shorter then MS-001.)



MECHANICAL DATA

P (R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE



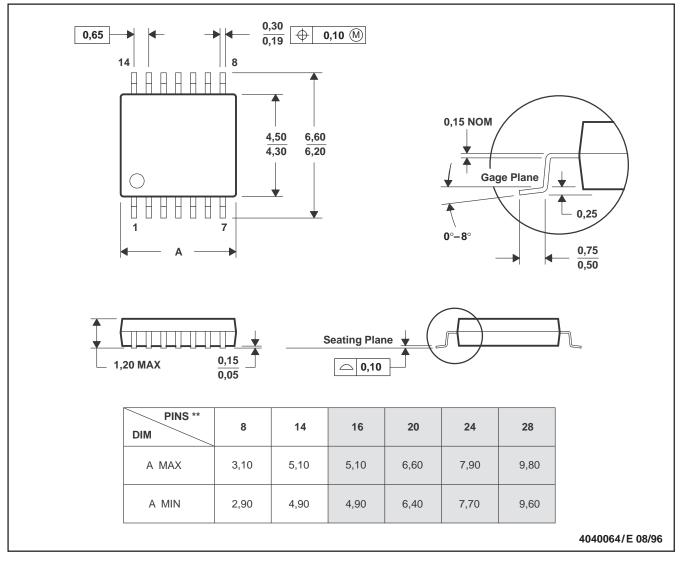
- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001

MECHANICAL DATA

PW (R-PDSO-G**)

14 PIN SHOWN

PLASTIC SMALL-OUTLINE PACKAGE

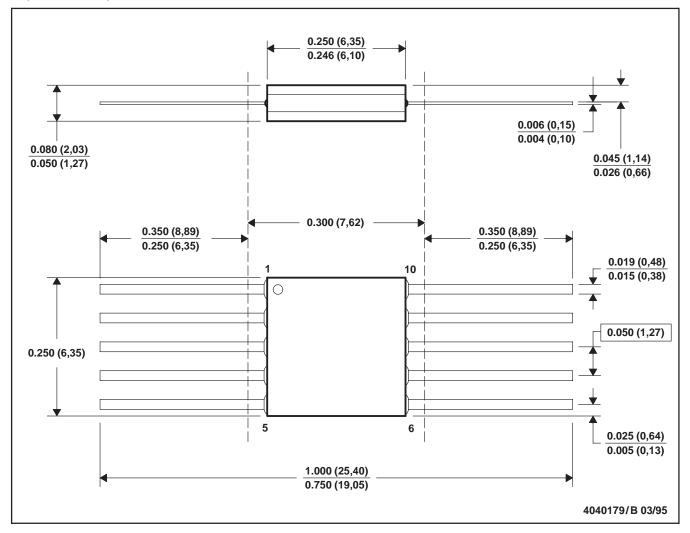


- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.
- D. Falls within JEDEC MO-153

MECHANICAL DATA

U (S-GDFP-F10)

CERAMIC DUAL FLATPACK

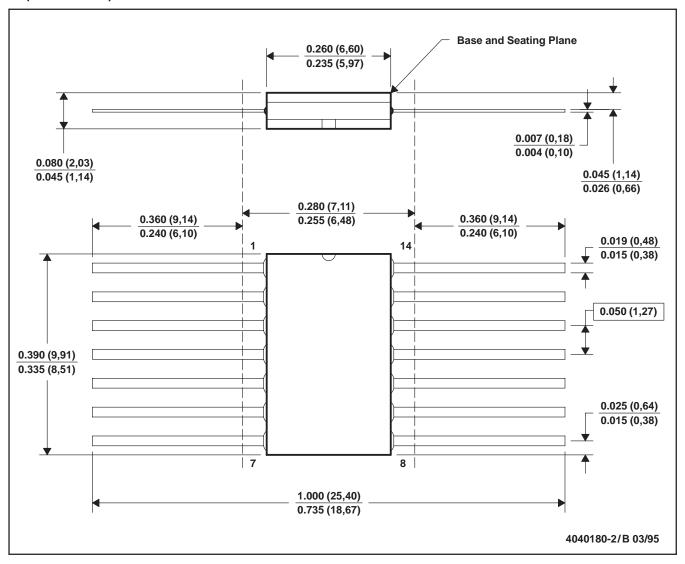


- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only.
- E. Falls within MIL STD 1835 GDFP1-F10 and JEDEC MO-092AA

MECHANICAL DATA

W (R-GDFP-F14)

CERAMIC DUAL FLATPACK



- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only.
- E. Falls within MIL STD 1835 GDFP1-F14 and JEDEC MO-092AB



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